# Power Transistor (-100V, -2A) 2SB1316

#### Features

- 1) Darlington connection for high DC current gain.
- 2) Built-in resistor between base and emitter.
- 3) Built-in damper diode.
- 4) Complements the 2SD2195 / 2SD1980.

#### Absolute maximum ratings (Ta = 25°C) Symb Collector-base voltage Collector-emitter voltage Emitter-base voltage Vcbo Vceo Vebo -100 V -100 tage A(DC) Collector current lc A(Pulse) \*1 Collector 2SB1580 w \*2 power dissipation 2SB1316 Pc 10 W(Tc=25°C) Junction temperature Ti 150 °C -55 Storage temperature Tstg to +150

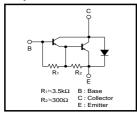
\*1 Single pulse Pw=100ms \*2 When mounted on a 40 x 40 x 0.7 mm ceramic board

#### Packaging specifications and hFE

Туре	2SB1580	2SB1316	
Package	MPT3	CPT3	
hfe	1k to 10k	1k to 10k	
Marking	BN*	-	
Code	T100	TL	
Basic ordering unit (pieces)	1000	2500	

\* Denotes hre

#### Equivalent circuit



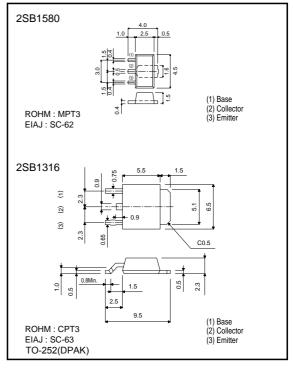
#### •Electrical characteristics (Ta = 25°C)

Symbol	Min.	Тур.	Max.	Unit	Conditions	
ВУсво	-100	-	-	V	Ic = -50μA	
BVCEO	-100	-	-	V	Ic = -5mA	
ВVево	-10	_	-	V	$I_E = -5mA$	
Ісво	-	-	-10	μΑ	Vcb = -100V	
Іево	-	-	-3	mA	$V_{EB} = -7V$	
VCE(sat)	-	-	-1.5	V	Ic/IB=-1A/-1mA	*
hfe	1000	-	10000	-	$V_{CE} = -2V$ , $I_C = -1A$	*
f⊤	-	50	-	MHz	$V_{CE} = -5V$ , $I_E = 0.1A$ , $f = 30MHz$	
Cob	-	35	-	pF	$V_{CB} = -10V$ , $I_E = 0A$ , $f = 1MHz$	
	BVCBO BVCEO BVEBO ICBO IEBO VCE(sat) hFE fr	ВVсво –100 ВVсво –100 ВVєво –10 Ісво – Ієво – Vcε(sat) – hrє 1000 fr –	BVCBO -100 -   BVCEO -100 -   BVEBO -10 -   ICBO - -   IEBO - -   VCE(sal) - -   hre 1000 -   fr - 50	BVCBO -100 - -   BVCEO -100 - -   BVEBO -10 - -   ICBO - - -   ICBO - - -   ICBO - - -   VCE(sat) - - -   VCE(sat) - - -   hFE 1000 - 10000   fr - 50 -	BV <sub>CBO</sub> -100 - - V   BV <sub>CEO</sub> -100 - - V   BV <sub>EBO</sub> -10 - - V   BV <sub>EBO</sub> -10 - - V   Iceo - - -10 μA   Ieeo - - -3 mA   Vce(sat) - - -1.5 V   hre 1000 - 10000 -   fr - 50 - MHz	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

\*Measured using pulse current.



#### •External dimensions (Unit : mm)



### Transistors

#### •Electrical characteristics curve

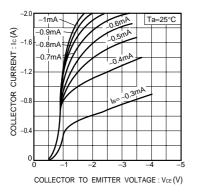


Fig.1 Grounded emitter output characteristics

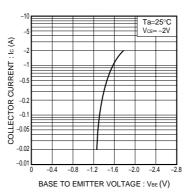


Fig.2 Grounded emitter propagation characteristics

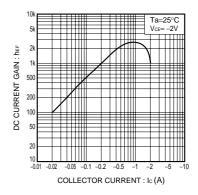


Fig.3 DC current gain vs. collector current

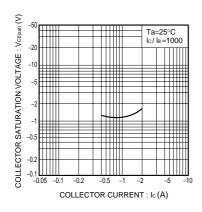


Fig.4 Collector-emitter saturation voltage vs. collector current

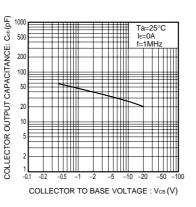


Fig.5 Collector output capacitance vs. collector-base voltage

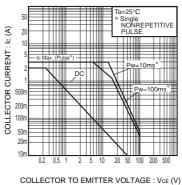
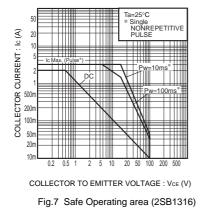


Fig.6 Safe Operating area (2SB1580)



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